Title (en)

Method of covering a device with a first layer of silicon nitride and with a second layer of a polyimide, and device covered by means of the method.

Title (de)

Verfahren zum Bedecken einer Anordnung mit einer ersten Schicht aus Siliconnitrid und mit einer zweiten Schicht aus einem Polyimid und eine nach diesem Verfahren bedeckte Anordnung.

Title (fr)

Procédé pour appliquer une première couche de nitrure de silicium et une seconde couche d'un polyimide sur un dispositif couvert par ce procédé.

Publication

EP 0251347 A1 19880107 (EN)

Application

EP 87200672 A 19870409

Priority

NL 8601041 A 19860423

Abstract (en)

The invention relates to a (semiconductor) device 1 at least one surface of which is covered with a first layer 3 of silicon nitride, which layer is made hydrophilic, after which a bonding agent is provided on the silicon nitride and a layer 4 of a photosensitive polyamide is then provided in which a pattern of apertures 5 is etched to give access to contact pads 2 for electrical connections, the bonding agent being a trialkoxysilane compound which comprises a primary amino group and which preferably comprises in addition at least one secondary amino group. The polyamide is finally converted to polyimide. By using the bonding agent, no undercutting occurs during etching the apertures in the polyamide layer and a good pattern definition is obtained.

IPC 1-7

H01L 21/312

IPC 8 full level

H01L 21/768 (2006.01); **H01L 21/3105** (2006.01); **H01L 21/312** (2006.01); **H01L 23/522** (2006.01)

CPC (source: EP US)

H01L 21/02118 (2013.01 - EP US); **H01L 21/0217** (2013.01 - EP US); **H01L 21/022** (2013.01 - EP US); **H01L 21/02304** (2013.01 - EP US); **H01L 21/02348** (2013.01 - US); **H01L 21/3105** (2013.01 - EP)

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